## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Splication of: Li, et al.

09/469,709 Serial No.:

Filed:

December 21, 1999

For:

High Through-Put Copper CMP With Reduced Erosion

And Dishing

**Assistant Commissioner for Patents** Washington, D.C. 20231

Dear Sir:

Group Art Unit: 1763

Examiner:

G. GOUDREAU

CERTIFICATE OF MAILING 37 CFR 1.8

I hereby certify that this correspondence is being deposited on March 23, 2001 with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

3/23/01

Date

## RESPONSE TO RESTRICTION REQUIREMENT

In response to the Office Action dated February 23, 2001, having a shortened statutory period for response set to expire on March 23, 2001, the Applicants elect claims 1-15 with traverse. The Commissioner is authorized to charge \$36.00 for two (2) additional claims to Deposit Account No. 20-0782/AMAT/3786/BTP, along with any other fees to make this response timely.

## THE PENDING CLAIMS:

Please cancel claims 1-29:

(Cancelled) A method of planarizing a wafer surface containing: 1.

an interlayer dielectric having an upper sufface and a plurality of spaced apart openings;

a barrier layer lining the opening and on the upper surface of the interlayer dielectric; and

copper (Cu) or a Cu alloy filling the openings and on the interlayer dielectric;

the method comprising the sequential steps of: